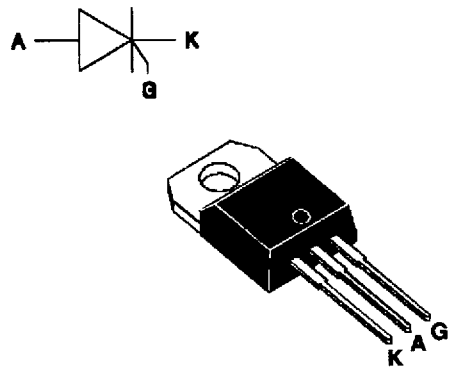
TXN/TYN 058 (G) ---> TXN/TYN 1008 (G)

SCR

FEATURES

- HIGH SURGE CAPABILITY
- HIGH ON-STATE CURRENT
- HIGH STABILITY AND RELIABILITY
- TXN Serie :
  INSULATED VOLTAGE = 2500V(RMS)
  (UL RECOGNIZED : E81734)



TO220AB
(Plastic)

DESCRIPTION

The TYN/TXN 058 ---> TYN/TXN 1008 Family of Silicon Controlled Rectifiers uses a high performance glass passivated chips technology.
This general purpose Family of Silicon Controlled Rectifiers is designed for power supplies up to 400Hz on resistive or inductive load.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter			Value	Unit
$I_{T(RMS)}$	RMS on-state current (180° conduction angle)	TXN TYN	Tc=100°C Tc=105°C	8	A
$I_{T(AV)}$	Average on-state current (180° conduction angle,single phase circuit)	TXN TYN	Tc=100°C Tc=105°C	5	A
I_{TSM}	Non repetitive surge peak on-state current (Tj initial = 25°C)		tp=8.3 ms	84	A
			tp=10 ms	80	
I^2t	I^2t value		tp=10 ms	32	A^2s
dI/dt	Critical rate of rise of on-state current Gate supply : I_G = 100 mA di_G/dt = 1 A/µs			50	A/µs
Tstg Tj	Storage and operating junction temperature range			- 40 to + 150 - 40 to + 125	°C °C
Tl	Maximum lead temperature for soldering during 10 s at 4.5 mm from case			260	°C

Symbol	Parameter	TYN/TXN							Unit
		058	108	208	408	608	808	1008	
V_{DRM} V_{RRM}	Repetitive peak off-state voltage Tj = 125 °C	50	100	200	400	600	800	1000	V

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
Rth (j-a)	Junction to ambient		60	°C/W
Rth (j-c) DC	Junction to case for DC	TXN	3.5	°C/W
		TYN	2.5	

GATE CHARACTERISTICS (maximum values)

$P_{G\ (AV)}$ = 1W P_{GM} = 10W (tp = 20 µs) I_{FGM} = 4A (tp = 20 µs) V_{RGM} = 5 V.

ELECTRICAL CHARACTERISTICS

Symbol	Test Conditions			Value		Unit
				BLANK	G	
I_{GT}	V_D=12V (DC) R_L=33Ω	Tj=25°C	MAX	15	25	mA
V_{GT}	V_D=12V (DC) R_L=33Ω	Tj=25°C	MAX	1.5		V
V_{GD}	V_D=V_{DRM} R_L=3.3kΩ	Tj= 110°C	MIN	0.2		V
tgt	V_D=V_{DRM} I_G = 40mA dI_G/dt = 0.5A/µs	Tj=25°C	TYP	2		µs
I_L	I_G= 1.2 I_{GT}	Tj=25°C	TYP	50		mA
I_H	I_T= 100mA gate open	Tj=25°C	MAX	30	45	mA
V_{TM}	ITM= 16A tp= 380µs	Tj=25°C	MAX	1.8		V
I_{DRM} I_{RRM}	V_{DRM} Rated V_{RRM} Rated	Tj=25°C	MAX	0.01		mA
		Tj= 110°C		2		
dV/dt	Linear slope up to V_D=67%V_{DRM} gate open	Tj= 110°C	MIN	200	500	V/µs
tq	V_D=67%V_{DRM} I_{TM}= 16A V_R= 25V dI_{TM}/dt=30 A/µs dV_D/dt= 50V/µs	Tj= 110°C	TYP	70		µs

Package	$I_{T(RMS)}$	V_{DRM} / V_{RRM}	Sensitivity Specification	
	A	V	BLANK	G
TXN (Insulated)	8	50	X	X
		100	X	X
		200	X	X
		400	X	X
		600	X	X
		800	X	X
		1000	X	X
TYN (Uninsulated)		50	X	X
		100	X	X
		200	X	X
		400	X	X
		600	X	X
		800	X	X
		1000	X	X

Fig.1 : Maximum average power dissipation versus average on-state current (TXN).

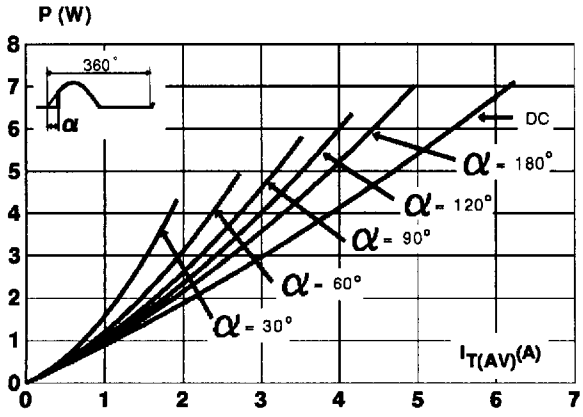


Fig.2 : Correlation between maximum average power dissipation and maximum allowable temperatures (T_{amb} and T_{case}) for different thermal resistances heatsink + contact (TXN).

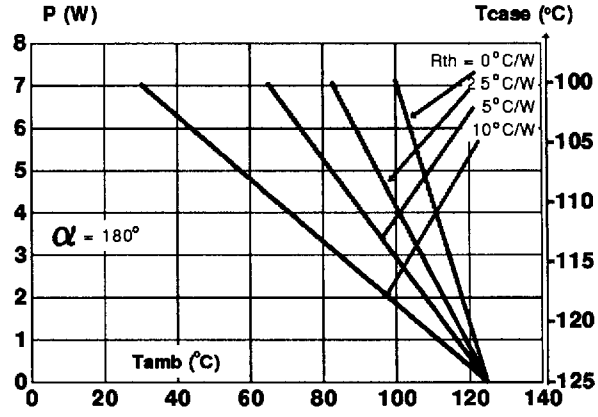


Fig.3 : Maximum average power dissipation versus average on-state current (TYN).

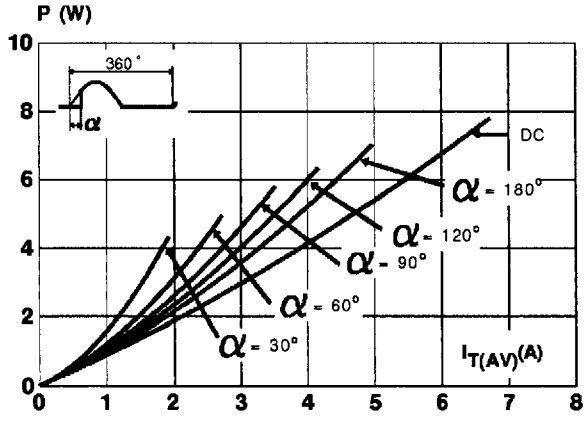


Fig.4 : Correlation between maximum average power dissipation and maximum allowable temperatures (T_{amb} and T_{case}) for different thermal resistances heatsink + contact (TYN).